

# A2T21H140-24SR3 :Part Detail

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## General Information

Part Number	A2T21H140-24SR3
Description	AIRFAST RF POWER LDMOS TRANSISTOR 2110-2170 MHz, 36 W AVG., 28 V
Product Line	21H140T
PTI	RHQH
Material Type	Tested Packaged Device
<a href="#">Life Cycle Description (code)</a>	PRODUCT RAPID GROWTH
Status	Active
<a href="#">Application/Qualification Tier</a>	10-YEARS APPLICATION LIFE

## Package Information

Package Type and Termination Count	Air Cavity 7
Package Description and Mechanical Drawing	<a href="#">NI-780S-4L2L</a>
Package Length (nominal)(mm)	20.570
Package Width (nominal)(mm)	9.780
Package Thickness (nominal)(mm)	3.750
Tape & Reel	Yes

## Environmental and Compliance Information

<a href="#">Pb-Free</a>	<a href="#">Contact Us</a>
<a href="#">RoHS Compliant</a>	<a href="#">Contact Us</a>
<a href="#">Material Composition Declaration (MCD)</a>	<a href="#">Contact Us</a>
<a href="#">RoHS Certificate of Analysis (CoA)</a>	<a href="#">Download RoHS CoA Report</a>
<a href="#">2nd Level Interconnect</a>	<a href="#">Contact Us</a>
Peak Package Body Temperature (PPT)(°C)	260
Maximum Time at Peak Temperature (s)	40
Number of Reflow Cycles	3
REACH SVHC	<a href="#">NXP REACH Statement</a>

## Manufacturing Information

Micron Size(μm)	6
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## Ordering Information

Minimum Package Quantity (MPQ)	250
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MPQ Container	REEL
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Exempt from Minimum Delivery Value	Yes
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Preferred Order Quantity (POQ)	250
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POQ Container	BOX
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Export Control Classification Number (US)	EAR99
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Harmonized Tariff (	
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CCATS Document	-
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ENC Status	-
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Other Trade Compliance Documents	-
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Budgetary Price excluding tax(US Currency)	-
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Order

## Operating Characteristics

Class	AB C
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Die Technology	LDMOS
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Efficiency (Typ) (%)	53.1
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Frequency (Min) (MHz)	2110
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Frequency Band (Min-Max) (MHz)	2110 to 2170
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Frequency Max (Max) (MHz)	2170
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Matching	I/O
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Output Power (Typ) (W) @ Intermodulation Level at Test Signal	36 @ AVG
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P3dB (Typ) (W)	169
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Power Gain (Typ) (dB) @ f (MHz)	17.4 @ 2110
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Sample Exception Availability	N
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Supply Voltage (Typ) (V)	28
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Test Signal	W-CDMA
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Thermal Resistance (Spec)	0.45
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